

Data Sheet

June 2, 2006

Dual 125MHz Video Current Feedback Amplifier

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The HA5023 is a wide bandwidth high slew rate dual amplifier optimized for video applications and gains between 1 and 10. It is a current feedback amplifier and thus yields less bandwidth degradation at high closed loop gains than voltage feedback amplifiers.

The low differential gain and phase, 0.1dB gain flatness, and ability to drive two back terminated 75 Ω cables, make this amplifier ideal for demanding video applications.

The current feedback design allows the user to take advantage of the amplifier's bandwidth dependency on the feedback resistor. By reducing R_F , the bandwidth can be increased to compensate for decreases at higher closed loop gains or heavy output loads.

The performance of the HA5023 is very similar to the popular Intersil HA-5020.

PART NUMBER	PART MARKING	TEMP. RANGE (°C)	PACKAGE	PKG. DWG. #		
HA5023IP	HA5023IP	-40 to 85	8 Ld PDIP	E8.3		
HA5023IPZ (Note)	HA5023IPZ	-40 to 85	8 Ld PDIP* (Pb-free)	E8.3		
HA5023IB	50231	-40 to 85	8 Ld SOIC	M8.15		
HA5023IB96	50231	-40 to 85	8 Ld SOIC Tape and Reel	M8.15		
HA5023IBZ (Note)	5023IBZ	-40 to 85	8 Ld SOIC (Pb-free)	M8.15		
HA5023IBZ96 (Note)	5023IBZ	-40 to 85	8 Ld SOIC Tape and Reel (Pb-free)	M8.15		
HA5023EVAL	VAL High Speed Op Amp DIP Evaluation Board					

Ordering Information

*Pb-free PDIPs can be used for through hole wave solder processing only. They are not intended for use in Reflow solder processing applications.

NOTE: Intersil Pb-free plus anneal products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

Features

• Wide Unity Gain Bandwidth
• Slew Rate 475V/µs
• Input Offset Voltage
Differential Gain 0.03%
Differential Phase 0.03°
Supply Current (per Amplifier)
• ESD Protection
 Guaranteed Specifications at ±5V Supplies

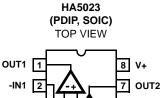
• Pb-Free Plus Anneal Available (RoHS Compliant)

Applications

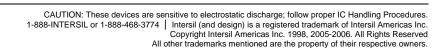
- · Video Gain Block
- Video Distribution Amplifier/RGB Amplifier
- Flash A/D Driver
- Current to Voltage Converter
- Medical Imaging
- Radar and Imaging Systems
- Video Switching and Routing

+IN1

Pinout



6 -IN2



Absolute Maximum Ratings

Voltage Between V+ and V- Terminals	
Operating Conditions Temperature Range40°C to 85°C Supply Voltage Range (Typical)	

Thermal Information

Thermal Resistance (Typical, Note 2)	θ_{JA} (°C/W)
PDIP Package*	130
SOIC Package	160
Maximum Junction Temperature (Note 1)	175°C
Maximum Junction Temperature (Plastic Package, Note	e 1) 150°C
Maximum Storage Temperature Range	5°C to 150°C
Maximum Lead Temperature (Soldering 10s) (SOIC - Lead Tips Only)	300°C
*Pb-free PDIPs can be used for through hole wave sol	der process-
ing only. They are not intended for use in Reflow solde applications.	r processing

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTES:

- 1. Maximum power dissipation, including output load, must be designed to maintain junction temperature below 175°C for die, and below 150°C for plastic packages. See Application Information section for safe operating area information.
- 2. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.
- 3. The non-inverting input of unused amplifiers must be connected to GND.
- 4. Output is protected for short circuits to ground. Brief short circuits to ground will not degrade reliability, however, continuous (100% duty cycle) output current should not exceed 15mA for maximum reliability.

PARAMETER	TEST CONDITIONS	(NOTE 9) TEST LEVEL	TEMP. (°C)	MIN	ТҮР	МАХ	UNITS
INPUT CHARACTERISTICS							
Input Offset Voltage (V _{IO})		А	25	-	0.8	3	mV
		А	Full	-	-	5	mV
Delta V _{IO} Between Channels		А	Full	-	1.2	3.5	mV
Average Input Offset Voltage Drift		В	Full	-	5	-	μV/°C
V _{IO} Common Mode Rejection Ratio	Note 5	А	25	53	-	-	dB
		А	Full	50	-	-	dB
V _{IO} Power Supply Rejection Ratio	$\pm 3.5 \text{V} \leq \text{V}_{\text{S}} \leq \ \pm 6.5 \text{V}$	А	25	60	-	-	dB
		А	Full	55	-	-	dB
Input Common Mode Range	Note 5	А	Full	±2.5	-	-	V
Non-Inverting Input (+IN) Current		А	25	-	3	8	μA
		А	Full	-	-	20	μA
+IN Common Mode Rejection	Note 5	А	25	-	-	0.15	μA/V
$(+I_{BCMR} = \frac{1}{+R_{IN}})$		А	Full	-	-	0.5	μA/V
+IN Power Supply Rejection	$\pm 3.5 \text{V} \leq \text{V}_{S} \leq \ \pm 6.5 \text{V}$	А	25	-	-	0.1	μA/V
		А	Full	-	-	0.3	μA/V
Inverting Input (-IN) Current		Α	25, 85	-	4	12	μA
		А	-40	-	10	30	μA
Delta - IN BIAS Current Between Channels		Α	25, 85	-	6	15	μA
		А	-40	-	10	30	μA

PARAMETER	TEST CONDITIONS	(NOTE 9) TEST LEVEL	TEMP. (°C)	MIN	ТҮР	МАХ	UNITS
-IN Common Mode Rejection	Note 5	А	25	-	-	0.4	μA/V
		А	Full	-	-	1.0	μA/V
-IN Power Supply Rejection	$\pm 3.5 V \le V_S \le \pm 6.5 V$	А	25	-	-	0.2	μA/V
		А	Full	-	-	0.5	μA/V
Input Noise Voltage	f = 1kHz	В	25	-	4.5	-	nV/√Hz
+Input Noise Current	f = 1kHz	В	25	-	2.5	-	pA/√Hz
-Input Noise Current	f = 1kHz	В	25	-	25.0	-	pA/√Hz
TRANSFER CHARACTERISTICS		ļ		Į	ļ	<u> </u>	ļ
Transimpedence	Note 11	А	25	1.0	-	-	MΩ
		А	Full	0.85	-	-	MΩ
Open Loop DC Voltage Gain	R _L = 400Ω, V _{OUT} = ±2.5V	А	25	70	-	-	dB
		А	Full	65	-	-	dB
Open Loop DC Voltage Gain	R _L = 100Ω, V _{OUT} = ±2.5V	А	25	50	-	-	dB
		А	Full	45	-	-	dB
OUTPUT CHARACTERISTICS					1		
Output Voltage Swing	R _L = 150Ω	А	25	±2.5	±3.0	-	V
		А	Full	±2.5	±3.0	-	V
Output Current	R _L = 150Ω	В	Full	±16.6	±20.0	-	mA
Output Current, Short Circuit	V _{IN} = ±2.5V, V _{OUT} = 0V	А	Full	±40	±60	-	mA
POWER SUPPLY CHARACTERISTICS		L	1	I	1	I	
Supply Voltage Range		А	25	5	-	15	V
Quiescent Supply Current		А	Full	-	7.5	10	mA/Op Amp
AC CHARACTERISTICS $(A_V = +1)$		I		1	1	I	L
Slew Rate	Note 6	В	25	275	350	-	V/µs
Full Power Bandwidth	Note 7	В	25	22	28	-	MHz
Rise Time	Note 8	В	25	-	6	-	ns
Fall Time	Note 8	В	25	-	6	-	ns
Propagation Delay	Note 8	В	25	-	6	-	ns
Overshoot		В	25	-	4.5	-	%
-3dB Bandwidth	V _{OUT} = 100mV	В	25	-	125	-	MHz
Settling Time to 1%	2V Output Step	В	25	-	50	-	ns
Settling Time to 0.25%	2V Output Step	В	25	-	75	-	ns

Electrical Specifications $V_{SUPPLY} = \pm 5V$, $R_F = 1k\Omega$, $A_V = +1$, $R_L = 400\Omega$, $C_L \le 10$ pF, Unless Otherwise Specified (Continued)

HA5023

PARAMETER	TEST CONDITIONS	(NOTE 9) TEST LEVEL	TEMP. (°C)	MIN	ТҮР	МАХ	UNITS
AC CHARACTERISTICS (A _V = +2, R _F	= 681Ω)					11	
Slew Rate	Note 6	В	25	-	475	-	V/µs
Full Power Bandwidth	Note 7	В	25	-	26	-	MHz
Rise Time	Note 8	В	25	-	6	-	ns
Fall Time	Note 8	В	25	-	6	-	ns
Propagation Delay	Note 8	В	25	-	6	-	ns
Overshoot		В	25	-	12	-	%
-3dB Bandwidth	V _{OUT} = 100mV	В	25	-	95	-	MHz
Settling Time to 1%	2V Output Step	В	25	-	50	-	ns
Settling Time to 0.25%	2V Output Step	В	25	-	100	-	ns
Gain Flatness	5MHz	В	25	-	0.02	-	dB
	20MHz	В	25	-	0.07	-	dB
AC CHARACTERISTICS (A _V = +10, R	F = 383Ω)					II	
Slew Rate	Note 6	В	25	350	475	-	V/µs
Full Power Bandwidth	Note 7	В	25	28	38	-	MHz
Rise Time	Note 8	В	25	-	8	-	ns
Fall Time	Note 8	В	25	-	9	-	ns
Propagation Delay	Note 8	В	25	-	9	-	ns
Overshoot		В	25	-	1.8	-	%
-3dB Bandwidth	V _{OUT} = 100mV	В	25	-	65	-	MHz
Settling Time to 1%	2V Output Step	В	25	-	75	-	ns
Settling Time to 0.1%	2V Output Step	В	25	-	130	-	ns
VIDEO CHARACTERISTICS	1					<u> </u>	
Differential Gain (Note 10)	R _L = 150Ω	В	25	-	0.03	-	%
Differential Phase (Note 10)	R _L = 150Ω	В	25	-	0.03	-	o

NOTES:

5. V_{CM} = ±2.5V. At -40°C Product is tested at V_{CM} = ±2.25V because Short Test Duration does not allow self heating.

6. $V_{\mbox{OUT}}$ switches from -2V to +2V, or from +2V to -2V. Specification is from the 25% to 75% points.

7. FPBW =
$$\frac{\text{Slew Rate}}{2\pi V_{\text{PEAK}}}$$
; $V_{\text{PEAK}} = 2V$.

8. $R_L = 100\Omega$, $V_{OUT} = 1V$. Measured from 10% to 90% points for rise/fall times; from 50% points of input and output for propagation delay.

9. A. Production Tested; B. Typical or Guaranteed Limit based on characterization; C. Design Typical for information only.

10. Measured with a VM700A video tester using an NTC-7 composite VITS.

4

11. V_{OUT} = ±2.5V. At -40°C Product is tested at V_{OUT} = ±2.25V because Short Test Duration does not allow self heating.

Test Circuits and Waveforms

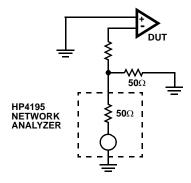


FIGURE 1. TEST CIRCUIT FOR TRANSIMPEDANCE MEASUREMENTS

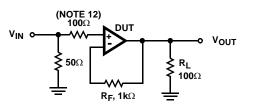


FIGURE 2. SMALL SIGNAL PULSE RESPONSE CIRCUIT

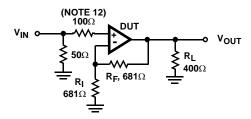
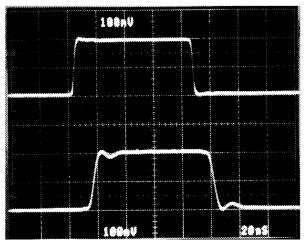


FIGURE 3. LARGE SIGNAL PULSE RESPONSE CIRCUIT

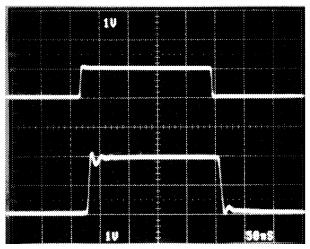
NOTE:

12. A series input resistor of \geq 100 Ω is recommended to limit input currents in case input signals are present before the HA5023 is powered up.



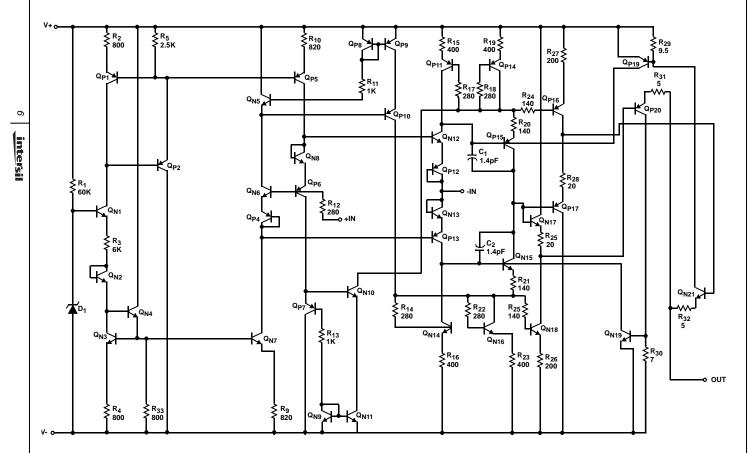
Vertical Scale: V_{IN} = 100mV/Div., V_{OUT} = 100mV/Div. Horizontal Scale: 20ns/Div.





Vertical Scale: $V_{IN} = 1V/Div.$, $V_{OUT} = 1V/Div.$ Horizontal Scale: 50ns/Div.

FIGURE 5. LARGE SIGNAL RESPONSE



Schematic Diagram (One Amplifier of Two)

FN3393.8 June 2, 2006

Application Information

Optimum Feedback Resistor

The plots of inverting and non-inverting frequency response, see Figure 8 and Figure 9 in the typical performance section, illustrate the performance of the HA5023 in various closed loop gain configurations. Although the bandwidth dependency on closed loop gain isn't as severe as that of a voltage feedback amplifier, there can be an appreciable decrease in bandwidth at higher gains. This decrease may be minimized by taking advantage of the current feedback amplifier's unique relationship between bandwidth and R_F. All current feedback amplifiers require a feedback resistor, even for unity gain applications, and R_F, in conjunction with the internal compensation capacitor, sets the dominant pole of the frequency response. Thus, the amplifier's bandwidth is inversely proportional to R_F. The HA5023 design is optimized for a 1000Ω R_F at a gain of +1. Decreasing R_F in a unity gain application decreases stability, resulting in excessive peaking and overshoot. At higher gains the amplifier is more stable, so RF can be decreased in a tradeoff of stability for bandwidth.

The table below lists recommended R_F values for various gains, and the expected bandwidth.

GAIN (A _{CL})	R_F (Ω)	BANDWIDTH (MHz)
-1	750	100
+1	1000	125
+2	681	95
+5	1000	52
+10	383	65
-10	750	22

PC Board Layout

The frequency response of this amplifier depends greatly on the amount of care taken in designing the PC board. The use of low inductance components such as chip resistors and chip capacitors is strongly recommended. If leaded components are used the leads must be kept short especially for the power supply decoupling components and those components connected to the inverting input.

Attention must be given to decoupling the power supplies. A large value (10μ F) tantalum or electrolytic capacitor in parallel with a small value (0.1μ F) chip capacitor works well in most cases.

A ground plane is strongly recommended to control noise. Care must also be taken to minimize the capacitance to ground seen by the amplifier's inverting input (-IN). The larger this capacitance, the worse the gain peaking, resulting in pulse overshoot and possible instability. It is recommended that the ground plane be removed under

7

traces connected to -IN, and that connections to -IN be kept as short as possible to minimize the capacitance from this node to ground.

Driving Capacitive Loads

Capacitive loads will degrade the amplifier's phase margin resulting in frequency response peaking and possible oscillations. In most cases the oscillation can be avoided by placing an isolation resistor (R) in series with the output as shown in Figure 6.

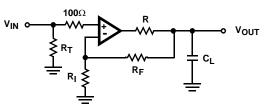


FIGURE 6. PLACEMENT OF THE OUTPUT ISOLATION RESISTOR, R

The selection criteria for the isolation resistor is highly dependent on the load, but 27Ω has been determined to be a good starting value.

Power Dissipation Considerations

Due to the high supply current inherent in dual amplifiers, care must be taken to insure that the maximum junction temperature (T_J, see Absolute Maximum Ratings) is not exceeded. Figure 7 shows the maximum ambient temperature versus supply voltage for the available package styles (Plastic DIP, SOIC). At $\pm 5V_{DC}$ quiescent operation both package styles may be operated over the full industrial range of -40°C to 85°C. It is recommended that thermal calculations, which take into account output power, be performed by the designer.

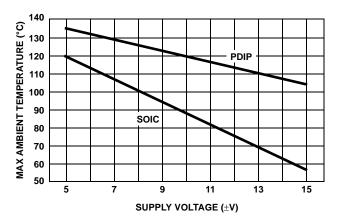
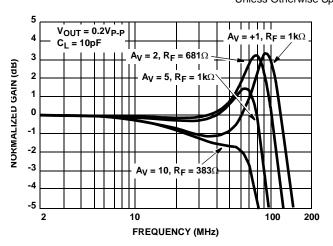


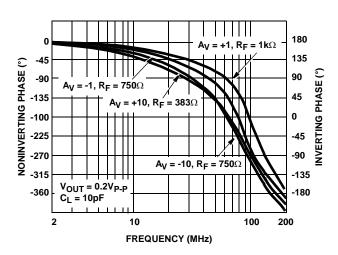
FIGURE 7. MAXIMUM OPERATING AMBIENT TEMPERATURE vs SUPPLY VOLTAGE

HA5023



Typical Performance Curves $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_F = 1k\Omega$, $R_L = 400\Omega$, $T_A = 25^{\circ}C$,
Unless Otherwise Specified

FIGURE 8. NON-INVERTING FREQENCY RESPONSE





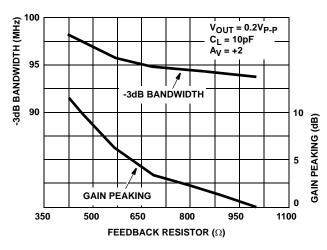


FIGURE 12. BANDWIDTH AND GAIN PEAKING vs FEEDBACK RESISTANCE

8

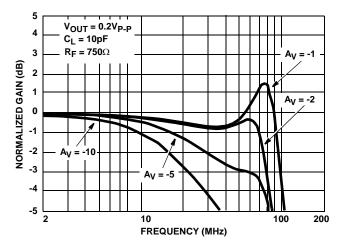


FIGURE 9. INVERTING FREQUENCY RESPONSE

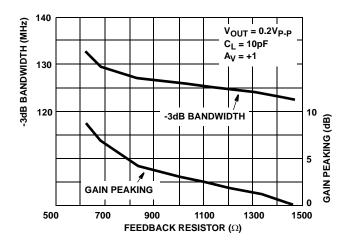
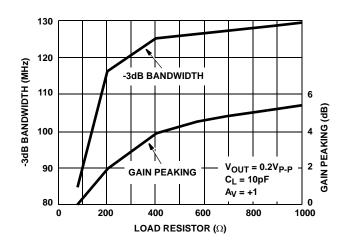
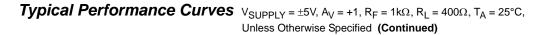


FIGURE 11. BANDWIDTH AND GAIN PEAKING vs FEEDBACK RESISTANCE







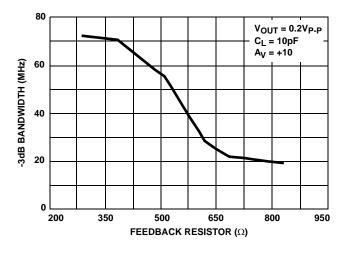


FIGURE 14. BANDWIDTH vs FEEDBACK RESISTANCE

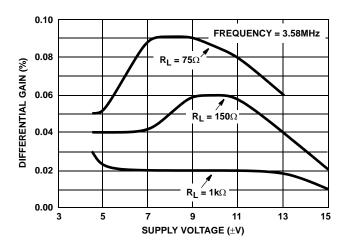
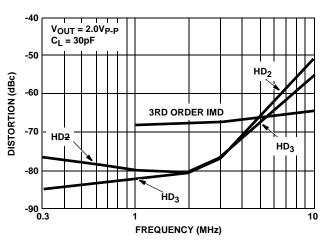


FIGURE 16. DIFFERENTIAL GAIN vs SUPPLY VOLTAGE





9

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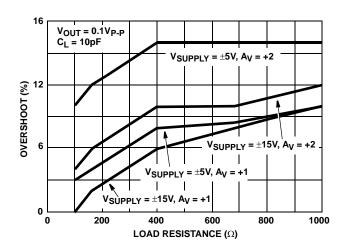


FIGURE 15. SMALL SIGNAL OVERSHOOT vs LOAD RESISTANCE

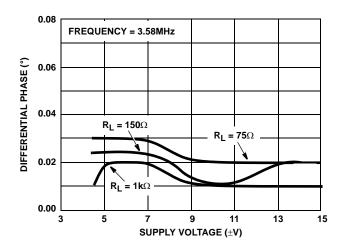


FIGURE 17. DIFFERENTIAL PHASE vs SUPPLY VOLTAGE

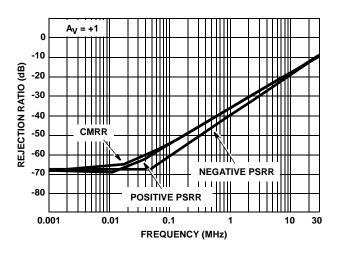
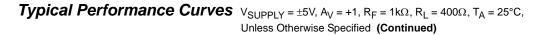


FIGURE 19. REJECTION RATIOS vs FREQUENCY



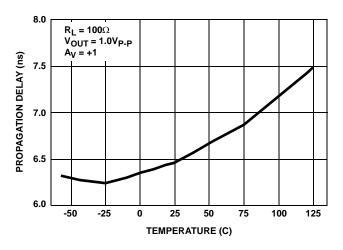


FIGURE 20. PROPAGATION DELAY vs TEMPERATURE

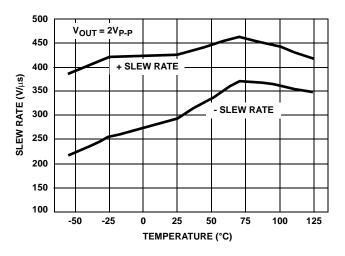


FIGURE 22. FIGURE 22. SLEW RATE vs TEMPERATURE

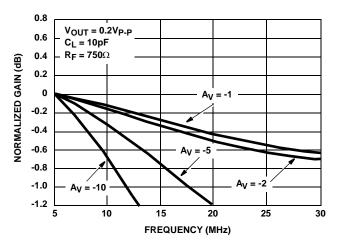
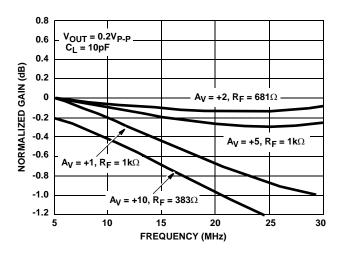


FIGURE 24. INVERTING GAIN FLATNESS vs FREQUENCY

10

12 R_{LOAD} = 100Ω V_{OUT} = 1.0V_{P-P} PROPAGATION DELAY (ns) 10 A_V = +10, R_F = 383Ω 8 A_V = +2, R_F = 681Ω 6 $A_V = +1, R_F = 1k\Omega$ 4 5 9 11 13 15 7 3 SUPPLY VOLTAGE (±V)

FIGURE 21. PROPAGATION DELAY vs SUPPLY VOLTAGE





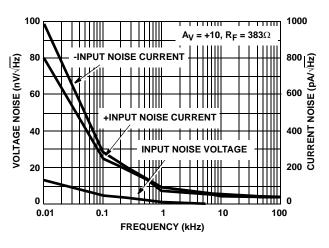
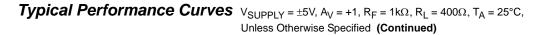


FIGURE 25. INPUT NOISE CHARACTERISTICS



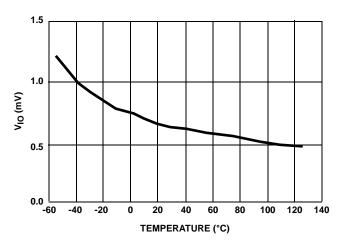


FIGURE 26. INPUT OFFSET VOLTAGE vs TEMPERATURE

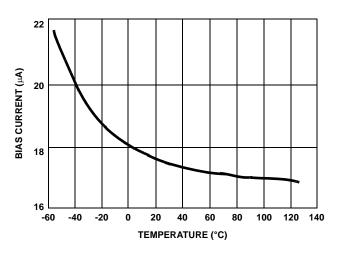


FIGURE 28. -INPUT BIAS CURRENT vs TEMPERATURE

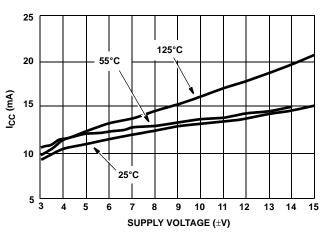


FIGURE 30. SUPPLY CURRENT vs SUPPLY VOLTAGE

11

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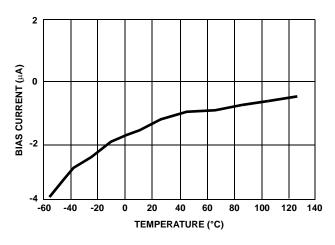


FIGURE 27. +INPUT BIAS CURRENT vs TEMPERATURE

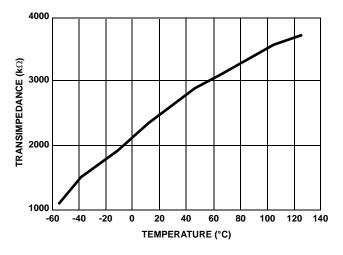


FIGURE 29. TRANSIMPEDANCE vs TEMPERATURE

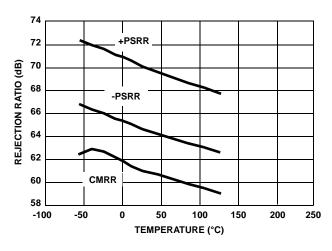
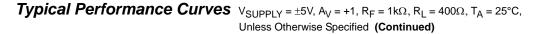


FIGURE 31. REJECTION RATIO vs TEMPERATURE



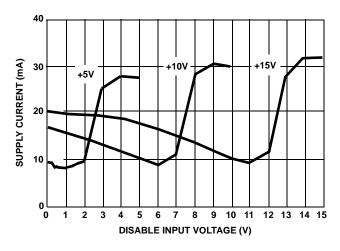


FIGURE 32. SUPPLY CURRENT vs DISABLE INPUT VOLTAGE

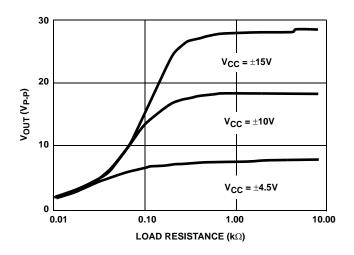


FIGURE 34. OUTPUT SWING vs LOAD RESISTANCE

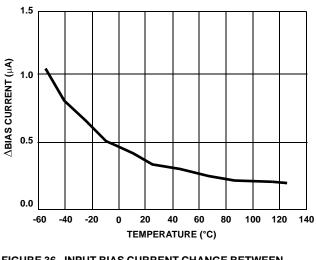


FIGURE 36. INPUT BIAS CURRENT CHANGE BETWEEN CHANNELS vs TEMPERATURE

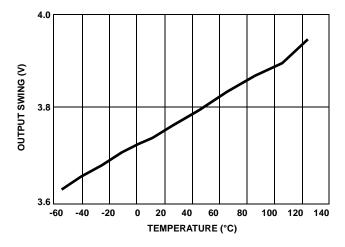


FIGURE 33. OUTPUT SWING vs TEMPERATURE

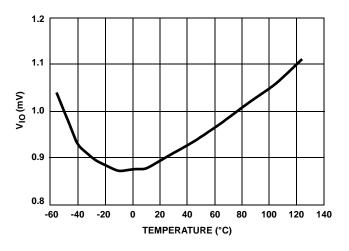


FIGURE 35. INPUT OFFSET VOLTAGE CHANGE BETWEEN CHANNELS vs TEMPERATURE

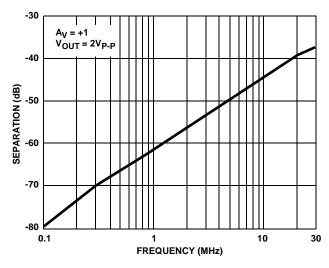
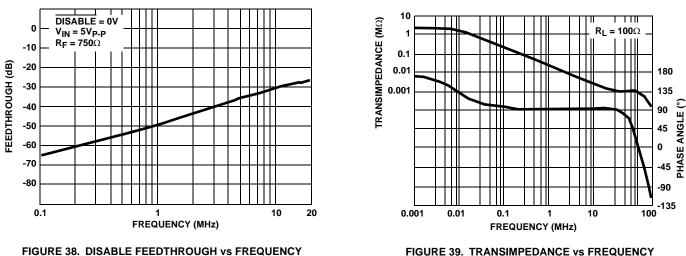


FIGURE 37. CHANNEL SEPARATION vs FREQUENCY

HA5023



Typical Performance Curves $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_F = 1k\Omega$, $R_L = 400\Omega$, $T_A = 25^{\circ}C$, Unless Otherwise Specified (Continued)

FIGURE 39. TRANSIMPEDANCE vs FREQUENCY

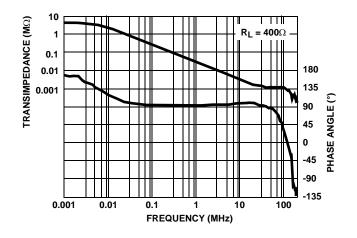


FIGURE 40. TRANSIMPEDENCE vs FREQUENCY

Die Characteristics

DIE DIMENSIONS:

 $1650 \mu m \ x \ 2540 \mu m \ x \ 483 \mu m$

METALLIZATION:

Type: Metal 1: AlCu (1%) Thickness: Metal 1: 8kÅ \pm 0.4kÅ

Type: Metal 2: AlCu (1%) Thickness: Metal 2: 16kÅ ±0.8kÅ

SUBSTRATE POTENTIAL (Powered Up):

V-

PASSIVATION:

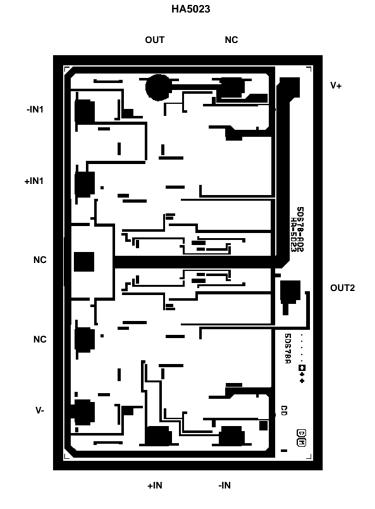
Type: Nitride Thickness: 4kÅ ±0.4kÅ

TRANSISTOR COUNT:

124

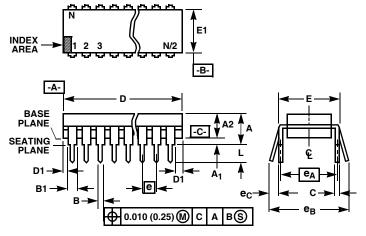
PROCESS:

High Frequency Bipolar Dielectric Isolation



Metallization Mask Layout

Dual-In-Line Plastic Packages (PDIP)



NOTES:

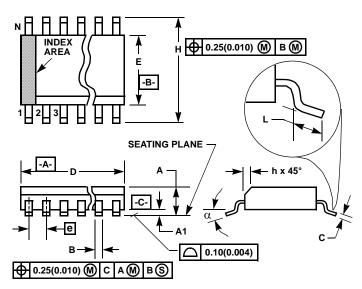
- 1. Controlling Dimensions: INCH. In case of conflict between English and Metric dimensions, the inch dimensions control.
- 2. Dimensioning and tolerancing per ANSI Y14.5M-1982.
- 3. Symbols are defined in the "MO Series Symbol List" in Section 2.2 of Publication No. 95.
- 4. Dimensions A, A1 and L are measured with the package seated in JEDEC seating plane gauge GS-3.
- D, D1, and E1 dimensions do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.010 inch (0.25mm).
- 6. E and eA are measured with the leads constrained to be perpendicular to datum -C-.
- 7. \mathbf{e}_B and \mathbf{e}_C are measured at the lead tips with the leads unconstrained. \mathbf{e}_C must be zero or greater.
- 8. B1 maximum dimensions do not include dambar protrusions. Dambar protrusions shall not exceed 0.010 inch (0.25mm).
- 9. N is the maximum number of terminal positions.
- Corner leads (1, N, N/2 and N/2 + 1) for E8.3, E16.3, E18.3, E28.3, E42.6 will have a B1 dimension of 0.030 - 0.045 inch (0.76 - 1.14mm).

E8.3 (JEDEC MS-001-BA ISSUE D) 8 LEAD DUAL-IN-LINE PLASTIC PACKAGE

	INC	HES	MILLIN	MILLIMETERS		
SYMBOL	MIN	MAX	MIN	MAX	NOTES	
А	-	0.210	-	5.33	4	
A1	0.015	-	0.39	-	4	
A2	0.115	0.195	2.93	4.95	-	
В	0.014	0.022	0.356	0.558	-	
B1	0.045	0.070	1.15	1.77	8, 10	
С	0.008	0.014	0.204	0.355	-	
D	0.355	0.400	9.01	10.16	5	
D1	0.005	-	0.13	-	5	
E	0.300	0.325	7.62	8.25	6	
E1	0.240	0.280	6.10	7.11	5	
е	0.100	BSC	2.54	BSC	-	
eA	0.300	BSC	7.62 BSC		6	
е _В	-	0.430	-	10.92	7	
L	0.115	0.150	2.93	3.81	4	
N	٤	3		9		

Rev. 0 12/93

Small Outline Plastic Packages (SOIC)



NOTES:

- 1. Symbols are defined in the "MO Series Symbol List" in Section 2.2 of Publication Number 95.
- 2. Dimensioning and tolerancing per ANSI Y14.5M-1982.
- Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion and gate burrs shall not exceed 0.15mm (0.006 inch) per side.
- Dimension "E" does not include interlead flash or protrusions. Interlead flash and protrusions shall not exceed 0.25mm (0.010 inch) per side.
- 5. The chamfer on the body is optional. If it is not present, a visual index feature must be located within the crosshatched area.
- 6. "L" is the length of terminal for soldering to a substrate.
- 7. "N" is the number of terminal positions.
- 8. Terminal numbers are shown for reference only.
- 9. The lead width "B", as measured 0.36mm (0.014 inch) or greater above the seating plane, shall not exceed a maximum value of 0.61mm (0.024 inch).
- 10. Controlling dimension: MILLIMETER. Converted inch dimensions are not necessarily exact.

M8.15 (JEDEC MS-012-AA ISSUE C) 8 LEAD NARROW BODY SMALL OUTLINE PLASTIC PACKAGE

	INC	IES	MILLIMETERS		
SYMBOL	MIN	MAX	MIN	MAX	NOTES
А	0.0532	0.0688	1.35	1.75	-
A1	0.0040	0.0098	0.10	0.25	-
В	0.013	0.020	0.33	0.51	9
С	0.0075	0.0098	0.19	0.25	-
D	0.1890	0.1968	4.80	5.00	3
Е	0.1497	0.1574	3.80	4.00	4
е	0.050	BSC	1.27 BSC		-
Н	0.2284	0.2440	5.80	6.20	-
h	0.0099	0.0196	0.25	0.50	5
L	0.016	0.050	0.40	1.27	6
Ν	8			8	7
α	0°	8°	0°	8°	-

Rev. 1 6/05

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